PATENT S/N_08/902,133

> IN THE UNITED STATES TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Serial No.: 08/902,133

Filed:

July 29, 1997

Title:

Docket: 303.356US1 DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ

Examiner: Valencia Wallace

Group Art Unit: 2815

ONLY MEMORY DEVICE

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT **AND CERTIFICATION UNDER 1.97(e)(2)**

Assistant Commissioner for Patents Washington, D.C. 20231

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 et. seq., the enclosed materials are brought to the attention of the Examiner for review in connection with the above-identified patent application. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, marked as being considered and initialled by the Examiner, be returned with the next official communication.

CERTIFICATION UNDER 37 C.F.R. § 1.97(e)(2)

Pursuant to 37 C.F.R. Section 1.97(e)(2), no item of information contained in the attached Supplemental Information Disclosure Statement and filed herewith was known to any individual designated in 37 C.F.R. Section 1.56 (c) more than three months prior to the filing of this Statement, to the best knowledge of the undersigned on this certification after making reasonable inquiry.

MAY 2 1 1999

TECHNOLOGY CENTER 2800

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Serial Number: 08/902,133

Filing Date: July 29, 1997

Title: DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE

Page 2 Dkt: 303.356US1

Applicants respectfully request consideration of these references during prosecution of the above-identified matter.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

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I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Assistant Commissioner of Patents, Washington, D.C. 20231 on May 1999.

 $\overline{}$

Name

Signature

PATENT S/N 08/902,133

IN THE UNITED STATES AND TRADEMARK OFFICE

MAY 2 0 1999

Applicant:

Leonard Forbes et al.

Serial No.:

08/902,133

Filed:

July 29, 1997

Title:

Docket: 303.356US1 RABLE PROGRAMMABLE READ DYNAMIC ELECTRICAL

ONLY MEMORY DEVICE

COMMUNICATION CONCERNING COPENDING APPLICATIONS

MAY 2 1 1999

Examiner: Valencia Wallace

Group Art Unit: 2815

Assistant Commissioner for Patents Washington, D.C. 20231

TECHNOLOGY CENTER 2800

Applicants would like to bring to the Examiner's attention the following list of copending applications for the above-identified patent application.

Serial No. 08/903,452	Filing Date 07/29/97	Attorney Docket No. 303.324US1	Title Transistor with Variable Electron Affinity Gate and Methods of Fabrication and Use
09/256,643	02/23/99	303.324US2	Transistor with Variable Electron Affinity Gate and Methods of Fabrication and Use
08/903,486	07/29/97	303.326US1	Silicon Carbide Gate Transistor and Fabrication Process
09/259,870	03/01/99	303.326US2	Silicon Carbide Gate Transistor and Fabrication Process
09/138,294	08/21/98	303.353US2	Transistor with Silicon Oxycarbide Gate and Methods of Fabrication
08/902,843	07/29/97	303.354US1	DEAPROM Having Amorphous Silicon Carbide Gate Insulator
09/135,413	08/14/98	303.354US2	DEAPROM Having Amorphous Silicon Carbide Gate Insulator
09/134,713	08/14/98	303.354US3	DEAPROM Having Amorphous Silicon Carbide Gate Insulator

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Serial Number: 08/902,133 Filing Date: July 29, 1997

DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE Title:

Serial No. 08/902,098	Filing Date 07/29/97	Attorney Docket No. 303.355US1	Title DEAPROM and Transistor with Gallium Nitride or Gallium Aluminum Nitride Gate
09/140,978	08/27/98	303.355US2	DEAPROM and Transistor with Gallium Nitride or Gallium Aluminum Nitride Gate
09/141,392	08/27/98	303.355US3	DEAPROM and Transistor with Gallium Nitride or Gallium Aluminum Nitride Gate
08/903,453	07/29/97	303.378US1	Carbonized Silicon Gate Insulators for Integrated Circuits
09/258,467	02/26/99	303.378US2	Carbonized Silicon Gate Insulators

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

for Integrated Circuits

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I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Assistant Commissioner of Patents, Washington, D.C. 20231 on May 1, 1999. Signature 1. Att mw

Name